

Bismuth Silicate ($\text{Bi}_{12}\text{SiO}_{20}$)

Surface Acoustic Wave (SAW) Devices
Bulk Acoustic Wave (BAW) Devices
Holographic Memory
Electro-optic Devices

Crystal Properties	Crystal Class	Cubic
	Point Group	23
	Space Group	$I2_3$
	Lattice Parameter	a 1.0103 nm
	Melting Point	890 °C
	Density	9.2 g/cm ³
	Hardness	4.5 Mohs
	Dielectric Constant	$\epsilon_{11}^S/\epsilon_0$ 42.7, $\epsilon_{33}^T/\epsilon_0$ 47.5
	Elastic Stiffness Coefficient	C_{11}^E 1.33, C_{44}^E 0.25 x 10 ¹¹ N/m ²
	Piezoelectric Strain Constant	e_{14} 1.01 C/m ²
	Transparency Range	470 ~ 7500 nm
	Electro-optic Coefficient	r_{41} 5.00 x 10 ⁻¹² m/V
	Refractive Index	2.45 (632.8 nm)
	Gradient of Refractive Index	≤ 5 x 10 ⁻⁵ /cm
Optic Activity	Left 20° mm ⁻¹ (632.8 nm)	
Transmittivity	69% (632.8 nm)	

Typical SAW Properties		V_s (m/s)	K_s^2 (%)	TCV (10 ⁻⁶ / °C)	TCD (10 ⁻⁶ / °C)
	[001] - [110]	1622	0.62	118	

Specifications	Boules	Section Size	45x45 [100], 45x50 [110]
		Typical Length	100 ~ 200 mm
		Typical Orientation	[100] [110], [111]
	Wafers	Typical Size	(20 ~ 40) x (100 ~ 200) mm
		Typical Thickness	2.0 mm
		Typical Orientation	[110] [001], [111]
		Front Side Polish	0.25 ~ 0.016 μm
		Back Side Lapping	10 ~ 15
		Flatness	≤ 30 μm
	Blocks	Bow	≤ 30 μm
		Typical Size	40x40x150 mm
Polish		0.016 μm	

